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Miyatake et al.

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(45) **Date of Patent:** **Aug. 12, 2014**

(54) **OPTICAL WAVEGUIDE DEVICE,
MANUFACTURING METHOD THEREFOR,
OPTICAL MODULATOR, POLARIZATION
MODE DISPERSION COMPENSATOR, AND
OPTICAL SWITCH**

(58) **Field of Classification Search**

None

See application file for complete search history.

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G02B 6/13 (2006.01)

G02F 1/03 (2006.01)

G02F 1/225 (2006.01)

(52) **U.S. Cl.**

CPC . **G02B 6/13** (2013.01); **G02F 1/225** (2013.01);

G02F 1/035 (2013.01); **G02F 1/0316** (2013.01)

USPC **385/2**; 385/3; 385/40

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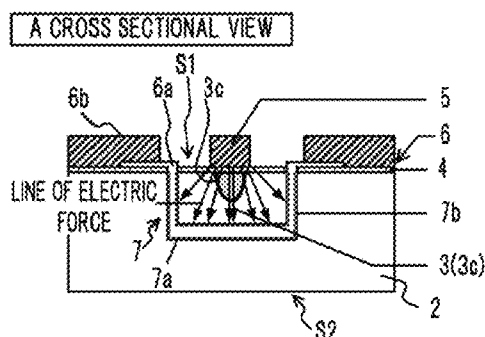
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(57) **ABSTRACT**

An optical waveguide device includes: a substrate which has an electro-optical effect; an optical waveguide which is formed on the substrate and/or inside the substrate; and an in-substrate electrode which is formed of a metal and provided inside the substrate.

3 Claims, 12 Drawing Sheets



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FIG. 1A

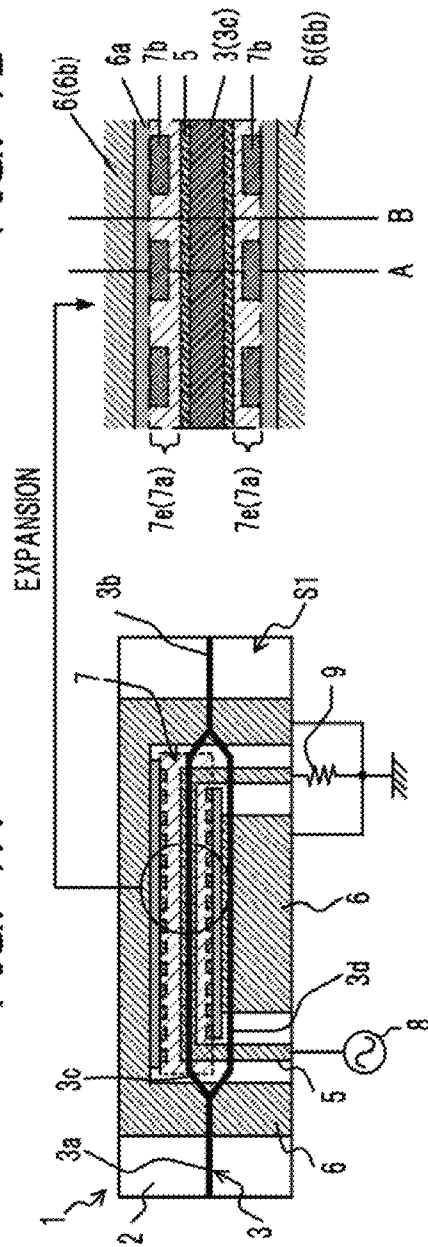
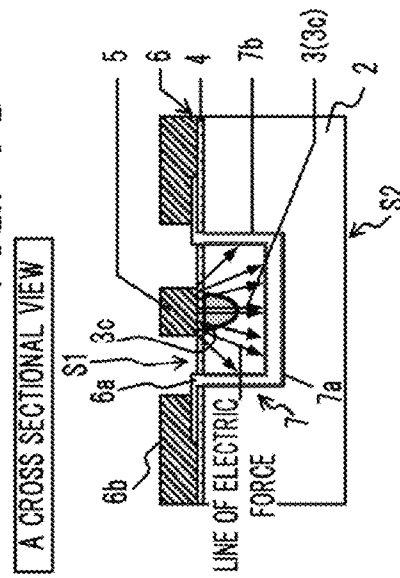
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FIG. 2A

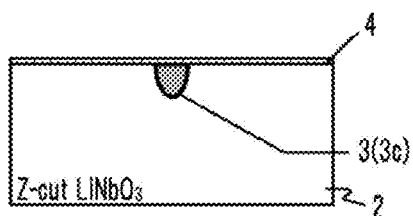


FIG. 2D

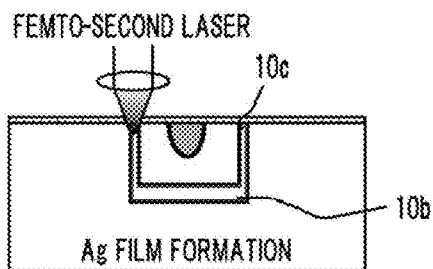


FIG. 2B

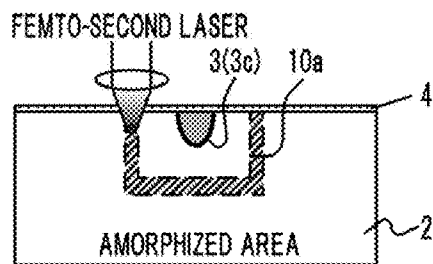


FIG. 2E

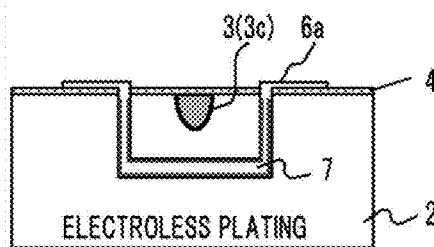


FIG. 2C

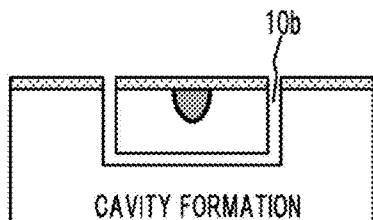


FIG. 2F

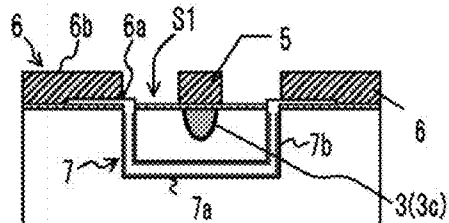
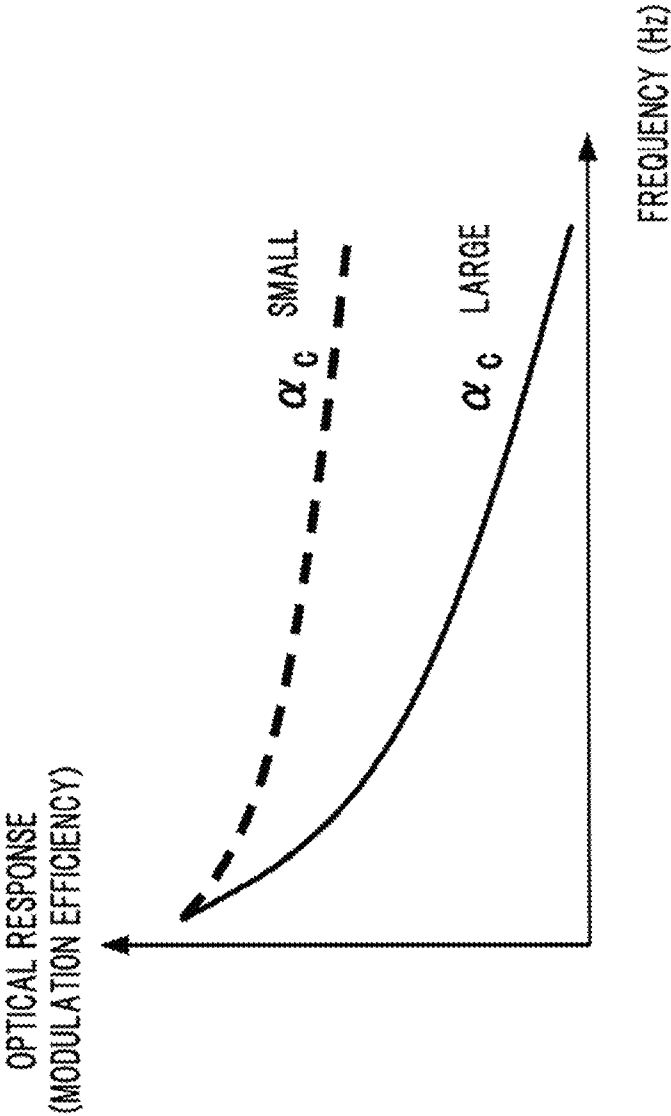


FIG. 3



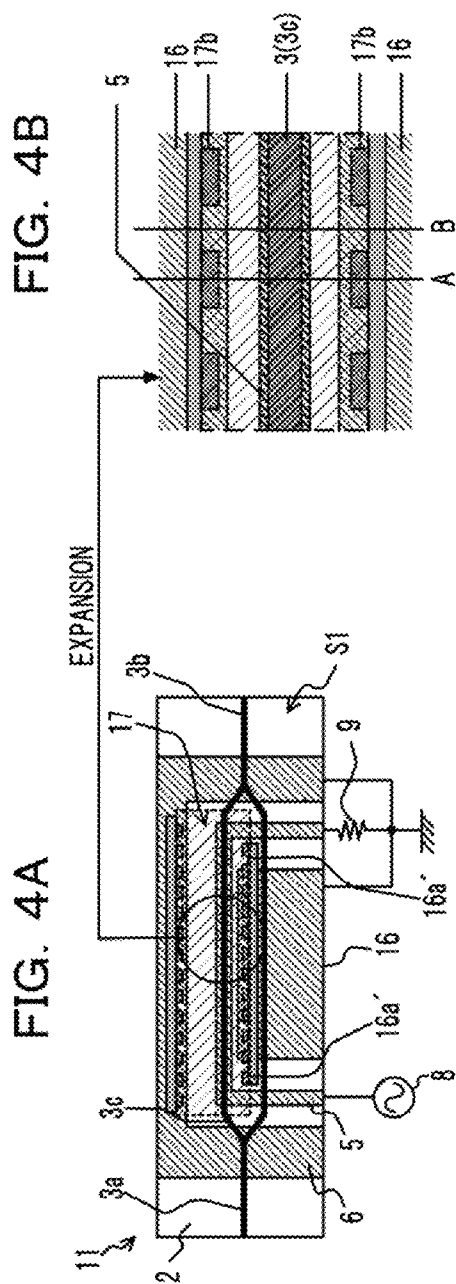


FIG. 4D

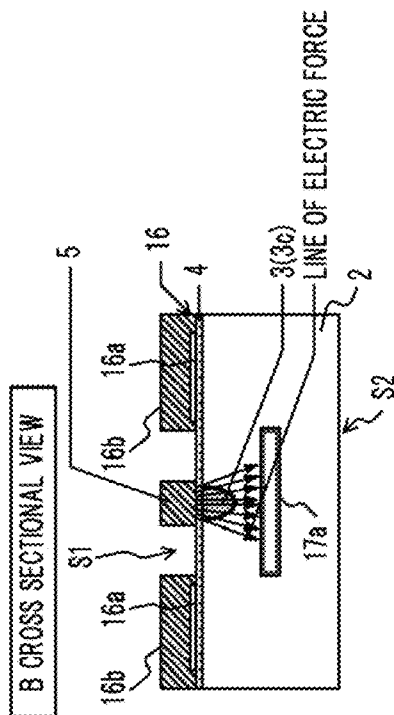


FIG. 4C

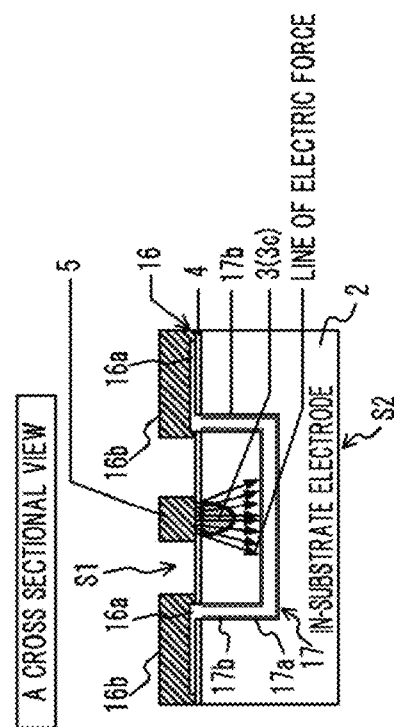
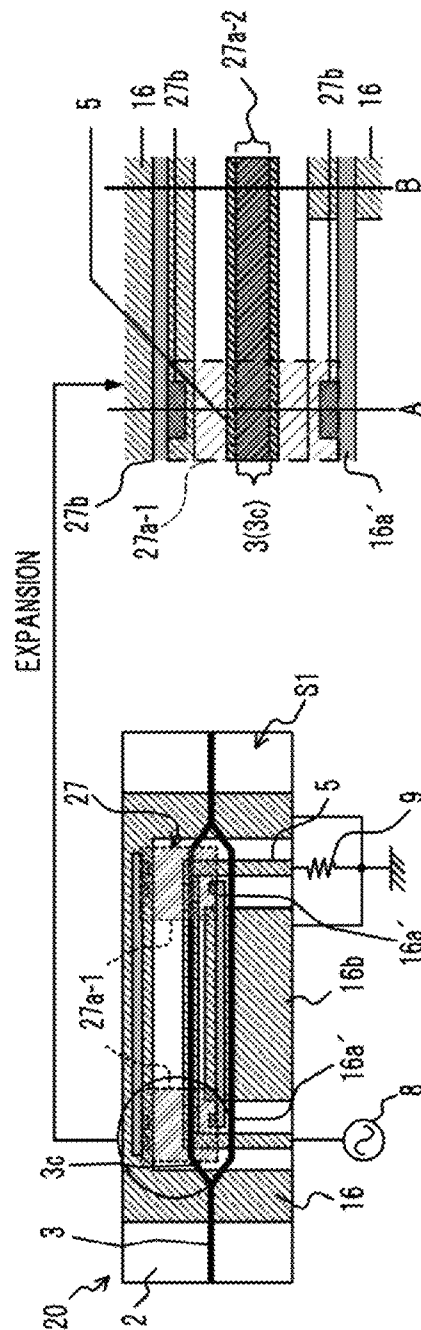
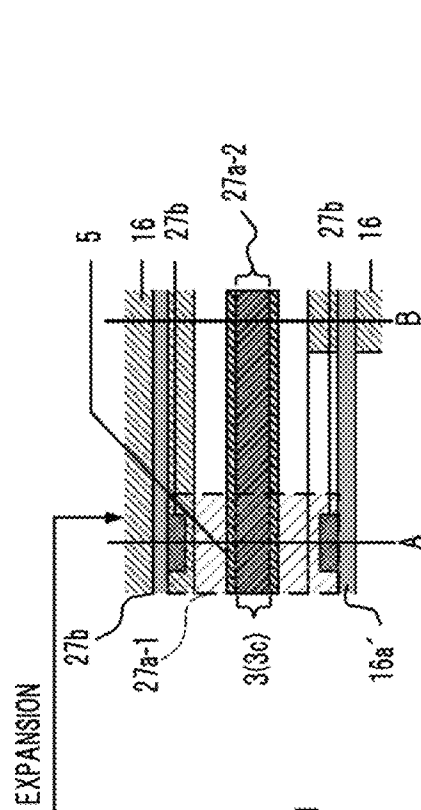


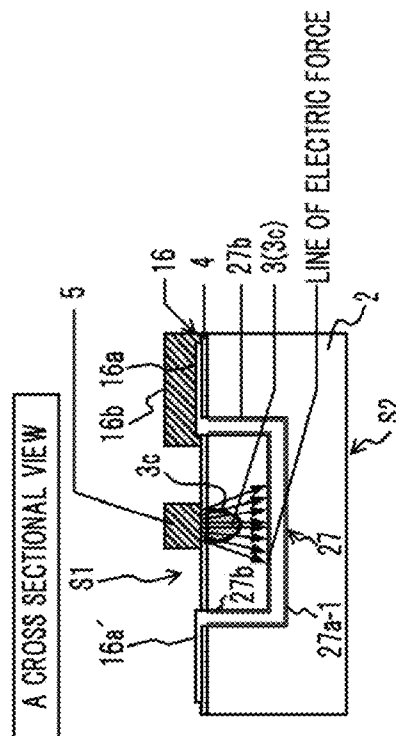
FIG. 5A



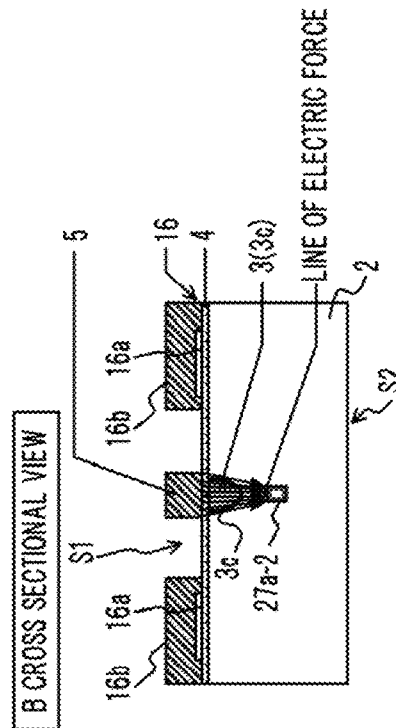
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ॐ नमो भगवते वासुदेवाय



7A
EG

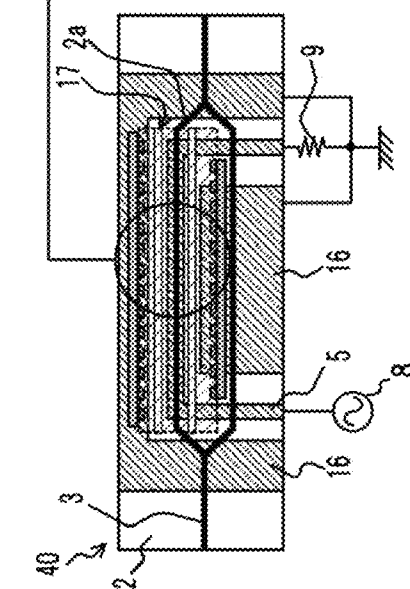
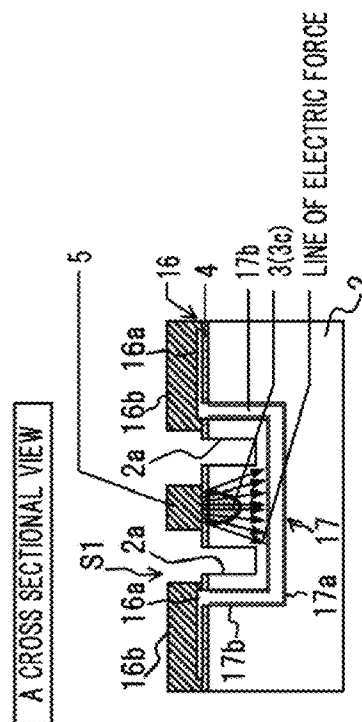
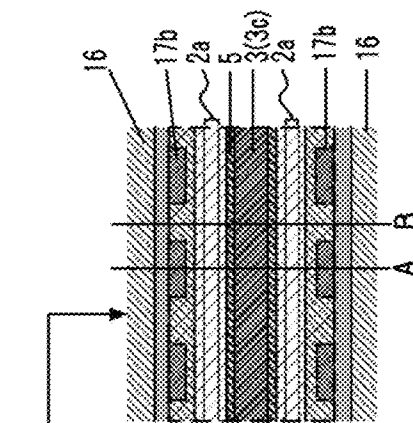


FIG. 7C



B7G4



7D
E.G.

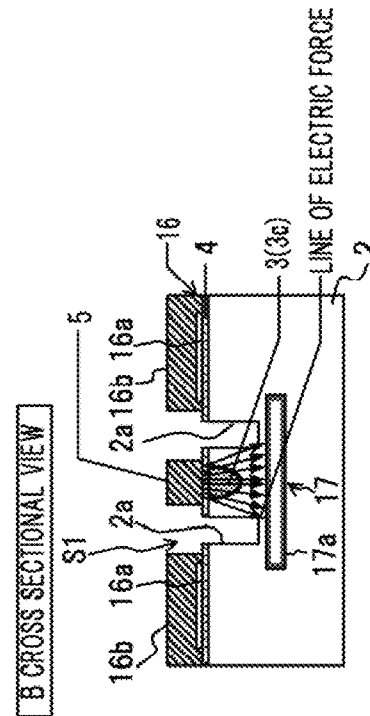


FIG. 8A

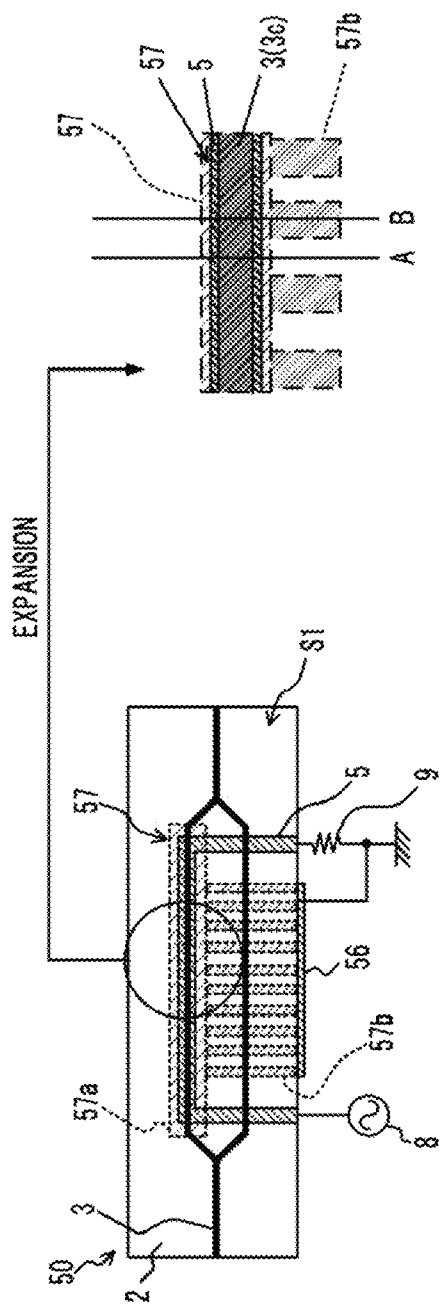


FIG. 8C

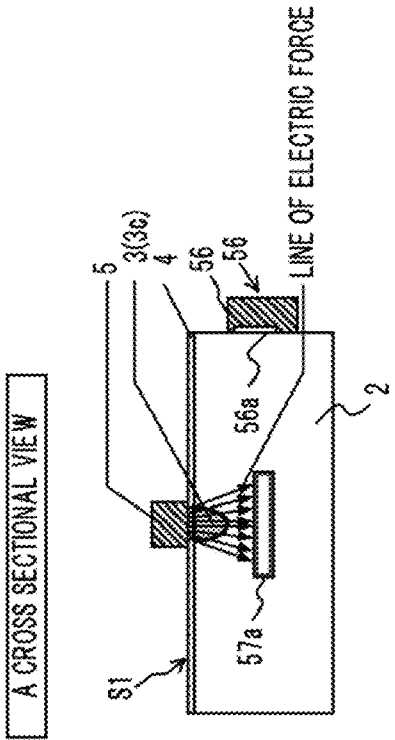


FIG. 8D

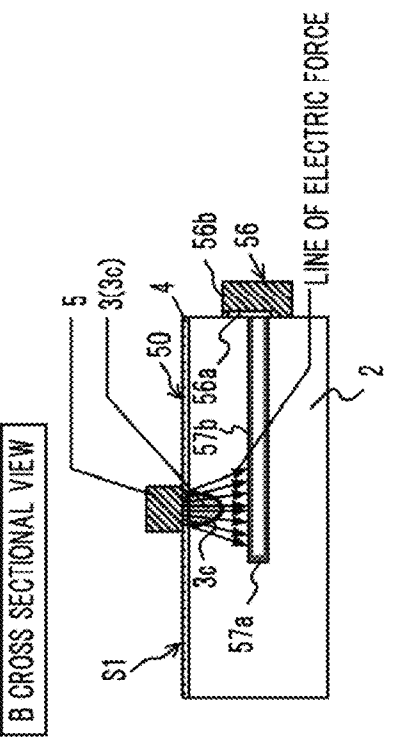


FIG. 9A

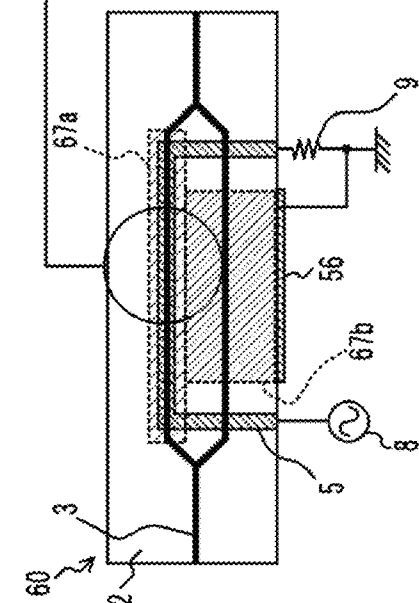


FIG. 9B

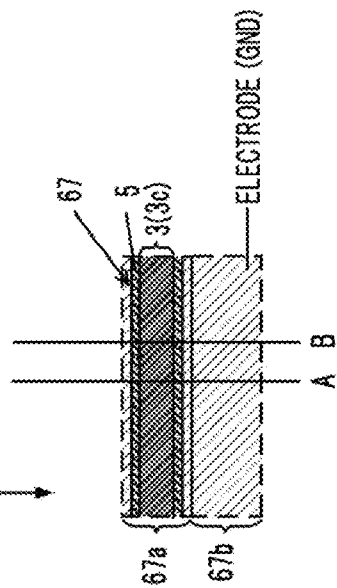


FIG. 9C

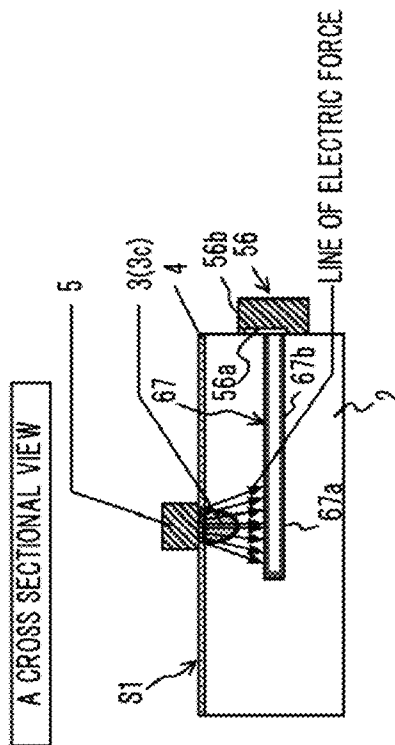


FIG. 9D

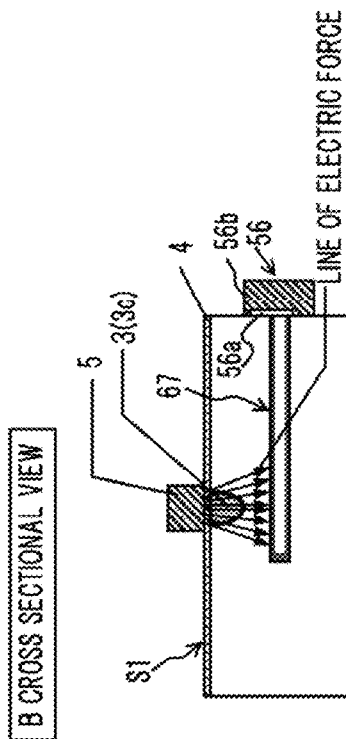


FIG. 10

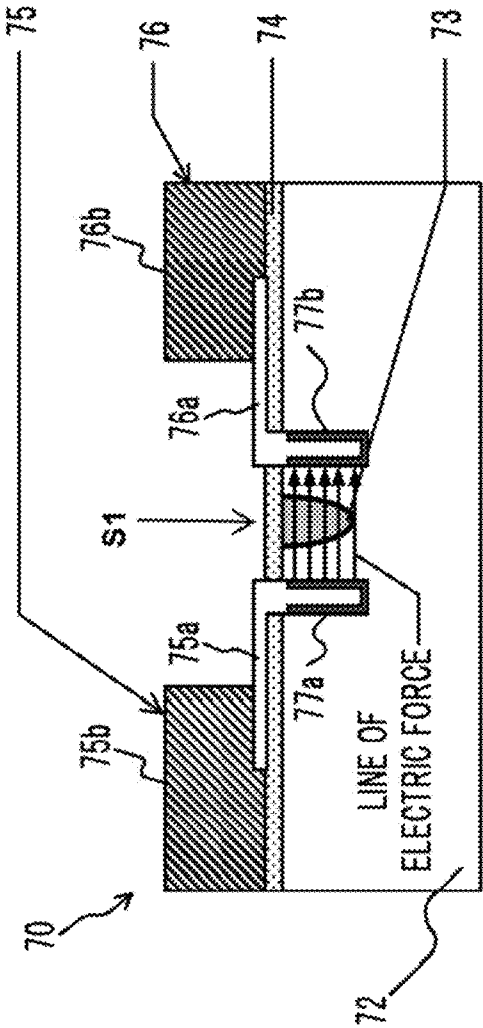


FIG. 11

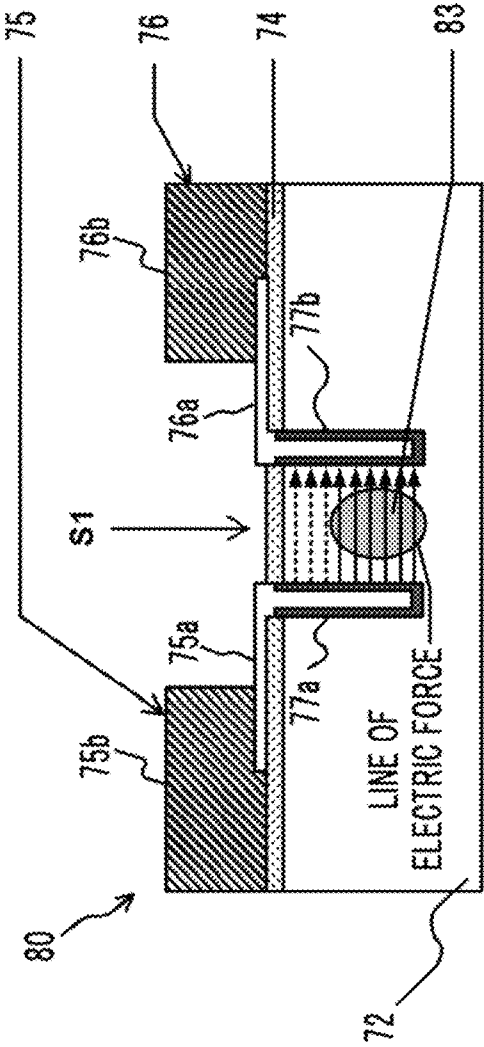
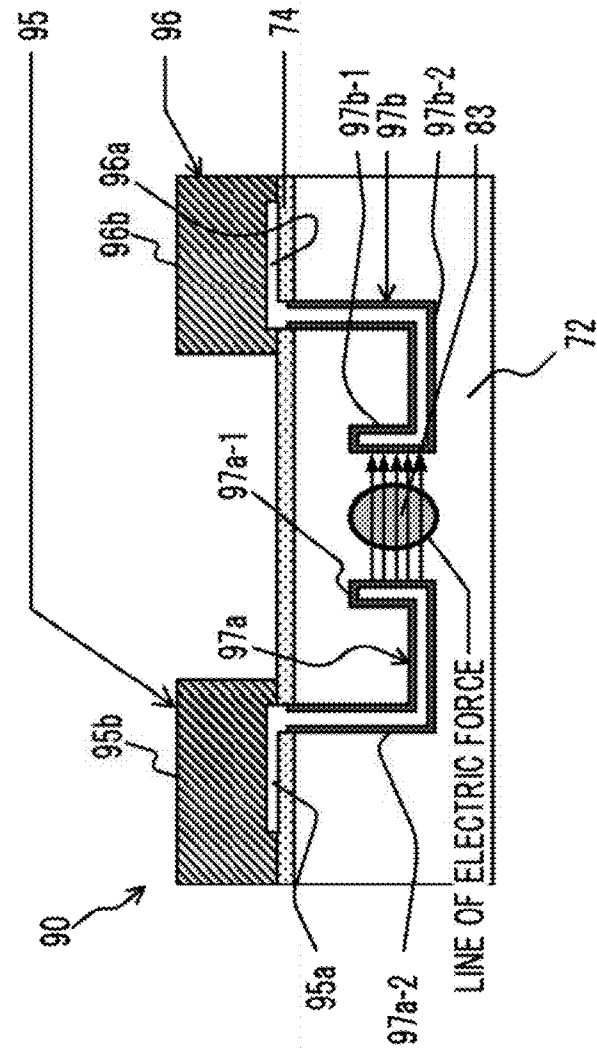


FIG. 12



1

**OPTICAL WAVEGUIDE DEVICE,
MANUFACTURING METHOD THEREFOR,
OPTICAL MODULATOR, POLARIZATION
MODE DISPERSION COMPENSATOR, AND
OPTICAL SWITCH**

**CROSS-REFERENCE TO RELATED
APPLICATIONS**

This application is a divisional of application Ser. No. 12/698,880, filed Feb. 2, 2010, which is based upon and claims the benefit of priority of the prior Japanese Patent Application No. 2009-022498, filed on Feb. 3, 2009, the entire contents of which are incorporated herein by reference.

FIELD

The embodiments discussed herein are related to an optical waveguide device, a manufacturing method therefor, an optical modulator, a polarization mode dispersion compensator, and an optical switch.

BACKGROUND

In recent years, miniaturization and power saving of transmission apparatuses for optical communications have been pursued. At present, a coplanar electrode structure, for example, is used in an optical waveguide device as a transmission apparatus. The coplanar electrode structure may control a refractive index based on an electric field supplied to the optical waveguide. However, a driving voltage is generally increased in order to provide control of the refractive index.

In addition to the coplanar electrode structure, a structure for concentrating lines of electric force on the optical waveguide by forming an electrode right under the optical waveguide has been proposed in Japanese Laid-Open Patent Publication No. 11-326853, for example.

According to a technique described in Japanese Laid-Open Patent Publication No. 11-326853, to epitaxially grow a lithium niobate (LiNbO₃:LN) thin-film, ZnO (a conductive crystal material) is employed as an electrode material formed directly under the waveguide. The conductive crystal material of the electrode matches a lattice constant of an LN crystal. However, a conductive crystal material such as ZnO has a resistance value that is expected to be higher than that of a metal in a low frequency area. Further, the resistance value of the conductive crystal material is expected to be even higher than that of the metal in a high frequency area.

Accordingly, using a conductive crystal material such as ZnO as an electrode driving at high-frequency voltage may cause large losses affecting the effectiveness of the electrode, which results in an increase of a related driving voltage. In general, the resistance value of the metal is relatively low compared to that of the conductive crystal material. However, in a technique described in Japanese Laid-Open Patent Publication No. 11-326853, the metal may not be used in place of the conductive crystal material at least because of the issue of matching the lattice constant.

SUMMARY

According to an aspect of the invention, an optical waveguide device includes: a substrate which has an electro-optical effect; an optical waveguide which is formed on the substrate and/or inside the substrate; and an in-substrate electrode which is formed of a metal and provided inside the substrate.

2

The object and advantages of the invention will be realized and attained by means of the elements and combinations particularly pointed out in the claims. It is to be understood that both the foregoing general description and the following detailed description are exemplary and explanatory and are not restrictive of the invention, as claimed.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1A illustrates a first embodiment;

FIG. 1B illustrates a first embodiment;

FIG. 1C illustrates a first embodiment;

FIG. 1D illustrates a first embodiment;

FIG. 2A illustrates an example of an intermediate step of a manufacturing process of an optical waveguide device illustrated in FIG. 1;

FIG. 2B illustrates an example of an intermediate step of a manufacturing process of an optical waveguide device illustrated in FIG. 1;

FIG. 2C illustrates an example of an intermediate of a manufacturing process of an optical waveguide device illustrated in FIG. 1;

FIG. 2D illustrates an example of an intermediate of a manufacturing process of an optical waveguide device illustrated in FIG. 1;

FIG. 2E illustrates an example of an intermediate of a manufacturing process of an optical waveguide device illustrated in FIG. 1;

FIG. 2F illustrates an example of an intermediate of a manufacturing process of an optical waveguide device illustrated in FIG. 1;

FIG. 3 illustrates a diagram of a relation between an optical response (modulation efficiency) and a frequency in the optical waveguide device;

FIG. 4A illustrates a second embodiment;

FIG. 4B illustrates a second embodiment;

FIG. 4C illustrates a second embodiment;

FIG. 4D illustrates a second embodiment;

FIG. 5A illustrates a third embodiment;

FIG. 5B illustrates a third embodiment;

FIG. 5C illustrates a third embodiment;

FIG. 5D illustrates a third embodiment;

FIG. 6A illustrates a fourth embodiment;

FIG. 6B illustrates a fourth embodiment;

FIG. 6C illustrates a fourth embodiment;

FIG. 6D illustrates a fourth embodiment;

FIG. 7A illustrates a fifth embodiment;

FIG. 7B illustrates a fifth embodiment;

FIG. 7C illustrates a fifth embodiment;

FIG. 7D illustrates a fifth embodiment;

FIG. 8A illustrates a sixth embodiment;

FIG. 8B illustrates a sixth embodiment;

FIG. 8C illustrates a sixth embodiment;

FIG. 8D illustrates a sixth embodiment;

FIG. 9A illustrates a seventh embodiment;

FIG. 9B illustrates a seventh embodiment;

FIG. 9C illustrates a seventh embodiment;

FIG. 9D illustrates a seventh embodiment;

FIG. 10 illustrates an eighth embodiment;

FIG. 11 illustrates a ninth embodiment; and

FIG. 12 illustrates a tenth embodiment.

**DETAILED DESCRIPTION OF THE
EMBODIMENTS**

With reference to the figures, embodiments will be described below. However, the embodiments described

3

below are examples. Various modifications and techniques that are not described below may be applied. That is, the described embodiments may be modified and performed without departing from the scope of the invention.

FIGS. 1A, 1B, 1C, and 1D are diagrams illustrating a first embodiment. In FIGS. 1A, 1B, 1C, and 1D, numeral 1 indicates an optical waveguide device. FIG. 1A is a top view of the optical waveguide device 1. FIG. 1B is an expanded view of a portion of FIG. 1A. FIG. 1C is an A cross sectional view of FIG. 1B. FIG. 1D is a B cross sectional view of FIG. 1B.

The optical waveguide device 1 includes a substrate 2, an optical waveguide 3, electrodes 5 and 6, and an in-substrate electrode 7. Numeral 4 illustrated in FIG. 1C and FIG. 1D indicates a buffer layer between the substrate 2 and the electrodes 5 and 6. Here, the substrate 2 has an electro-optical effect and changes the refractive index of the optical waveguide 3 based on an electric field (a line of electric force in FIGS. 1C and 1D) applied in a direction approximately and/or substantially vertical (perpendicular) to a first surface S1 of the substrate 2 or a second surface S2. The second surface S2 in FIGS. 1C and 1D is a back surface of the substrate S2. For example, a Z-cut lithium niobate substrate may be used. A substrate formed of a single electro-optic crystal may also be used.

The optical waveguide 3 is formed in and/or on the first surface S1 of the substrate 2. As illustrated in FIG. 1A, the optical waveguide 3 includes an incident waveguide unit 3a and a projection waveguide unit 3b and may be formed in a Mach-Zehnder interferometer having branching waveguide units 3c and 3d between the incident waveguide unit 3a and the projection waveguide unit 3b. The pattern of the optical waveguide 3 is an example. Any other pattern may be used to form the optical waveguide 3. Moreover, the optical waveguide 3 may be formed inside the substrate 2.

Furthermore, the electrodes 5 and 6 may be formed to operate to correspond to the branching waveguide units 3c and 3d. As illustrated in FIGS. 1A, 1B, 1C, and 1D, the electrode 5 is formed on the top of the branching waveguide unit 3c as a traveling wave electrode used to apply an electric field to the branching waveguide unit 3c. A high-frequency electrical signal according to transmission data is supplied from one end of the electrode 5 by a signal source 8, and the other end is terminated by a termination resistor 9.

The electrode 6 is a ground electrode formed at a distance from the electrode 5 and includes a first electrode unit 6a, which is used to be electrically connected to the in-substrate electrode 7 described below, and includes a second electrode unit 6b that is connected to the first electrode unit 6a. The first electrode unit 6a illustrated in FIGS. 1B, 1C, and 1D indicates an area formed to be thinner than the second electrode unit 6b of the electrode 6. According to the present embodiment, the first electrode unit 6a extends from the second electrode unit 6b in a direction towards the electrode 5.

Furthermore, the in-substrate electrode 7 is formed of metal such as copper. As illustrated in FIG. 2A through FIG. 2F, a cavity is formed inside the substrate 2 that is to be the in-substrate electrode 7. The formed cavity is filled with a metallic material. In this case, the in-substrate electrode 7 includes a first internal electrode unit 7a and a via part 7b.

The first internal electrode unit 7a is formed between the branching waveguide unit 3c and the second surface S2 of the substrate 2 and includes a surface corresponding to a surface to which a signal electrode 5 applies the electric field (the line of electric force) in the direction approximately and/or substantially vertical (perpendicular) to the first surface S1. That is, as illustrated in FIG. 1C and FIG. 1D, the first internal

4

electrode unit 7a may be formed to have a surface that is substantially parallel to the first surface S1.

As illustrated in FIG. 1B through FIG. 1D, the first internal electrode unit 7a is formed to range from an upstream side to a downstream side in a light propagation direction in the branching waveguide unit 3c and is wider than the width of the signal electrode 5. In FIG. 1B, the area of the first internal electrode unit 7a, which is wider than the width of the signal electrode 5, is illustrated as an area 7e.

The via part (conduction via) 7b is an example of a first connection unit that electrically connects the first internal electrode unit 7a and a ground electrode 6. As illustrated in FIG. 1C, the via part 7b is formed along both edges of the width direction of the first internal electrode unit 7a. According to the present embodiment, a plurality of via parts 7b are formed at intervals along the above-described area 7e formed to be extended in the first internal electrode unit 7a. The via parts 7b provide a conductive connection between the first internal electrode unit 7a and the first electrode unit 6a composing the ground electrode 6, for example.

According to the present embodiment, the areas 7e are formed on the both sides of the signal electrode 5, and the via parts 7b are formed at intervals along the edges of the areas 7e on the both sides of the signal electrode 5. The A cross sectional view illustrated in FIG. 1C includes a cross sectional view of the via part 7. The B cross sectional view illustrated in FIG. 1D does not include the cross sectional view of the via part 7b because the B cross sectional view is a cross section view of a portion between the via parts 7b.

Next, an example of a manufacturing process of the optical waveguide device 1 illustrated in FIG. 1 will be described by using FIG. 2A through FIG. 2F. As illustrated in FIG. 2A, on the first surface S1 of the LN substrate 2, the optical waveguide 3 is formed by a titanium (Ti) diffusion method or the like, and then a buffer layer 4 is formed.

Next, a cavity is formed in a part where the in-substrate electrode 7 is required to be formed in the substrate 2. For example, condensing and radiating of an ultrashort pulse laser is performed onto a part where the in-substrate electrode 7 is to be formed. Then selective etching is performed after the part is amorphized.

Specifically, a femto-second laser as an example of the ultrashort pulse laser is radiated onto a part where the first internal electrode unit 7a is to be formed under the branching waveguide unit 3c viewed from the first surface S1 and onto a part where the via part 7b is required to be formed, and then the substrate 2 is amorphized (see FIG. 2B).

The femto-second laser is radiated onto the substrate 2, so that a part of the substrate 2 in which focus positions of the femto-second laser are connected is amorphized. Accordingly, for example, a specified area in the substrate 2 may be amorphized by moving the substrate 2 which is fixed to a base in such a way that a track of the focus positions of the femto-second laser follows the above-described part where the in-substrate electrode 7 is required to be formed.

Next, as illustrated in FIG. 2C, a part 10a irradiated with the above-described femto-second laser is radiated and is wet-etched by acid or potassium hydroxide (KOH), for example. The amorphized area corresponding to the part where the via part 7b is formed operates as an approach path through which etchant penetrates into a forming unit of the first internal electrode unit 7a. This makes it possible to form a cavity in the part where the first internal electrode unit 7a is formed and in the part where the via part 7b is formed. Numeral 10b as illustrated in FIG. 2C indicates a cavity formed by the above-described process for forming a cavity.

5

After the cavity **10b** is formed as described above, the cavity **10b** is filled with metal. For example, as illustrated in FIG. 2D, the cavity **10b** formed as described above is filled with metallic salt (for example, AgNO_3), and the femto-second laser is radiated onto an inner wall of the cavity **10b**. This makes it possible to precipitate the metal (for example, Ag) on the inner wall of the cavity **10b**. The precipitated metal may be formed like a thin film (see a metal thin film **10c** illustrated in FIG. 2D).

As illustrated in FIG. 2E, electroless plating is performed on the cavity **10b** with the metal thin film **10c**, and then metal (for example, Cu) is embedded in the cavity **10b**. In this manner, the in-substrate electrode **7** is formed. In addition to the above-described formation area of the in-substrate electrode **7**, the first electrode unit **6a** composing a part of the ground electrode **6** formed on the top of the substrate **2** may be formed in the process for filling metal by the electroless plating.

Furthermore, after the in-substrate electrode **7** is formed as described above, the signal electrode **5** and the ground electrode **6** are formed on the first surface **S1** as illustrated in FIG. 2F. At this time, to set application voltage to the first internal electrode unit **7a** from the first surface **S1** side, the first internal electrode unit **7a** is connected to the ground electrode **6** via the via part **7b**. Specifically, an electrode **6b**, which is to be electrically connected to the first electrode unit **6a** that is formed when the via part **7b** is formed, is formed.

In the above-described process for forming the cavity **10b**, the cavity part corresponding to a formation part of the via part **7b** is formed in the direction vertical (perpendicular) to the first surface **S1** and may also be formed in a direction oblique to the substrate **2**. Moreover, to form the cavity **10b**, instead of conducting the above-described process, an ablation may be performed on the part where the in-substrate electrode **7** is to be formed. Specifically, after the above-described process in FIG. 2A, the cavity **10b** illustrated in FIG. 2C may be formed by using the ablation of the substrate **2** by radiating the femto-second laser instead of conducting the above-described process.

As described above, the optical waveguide device **1** may change the refractive index of the branching waveguide unit **3c** according to the driving voltage that is applied to the signal electrode **5**. This makes it possible to modulate a light that is input from the incident waveguide unit **3a** of the optical waveguide **3** composing the Mach-Zehnder interferometer, and the light is output as a modulated light from the projection waveguide unit **3b**. In other words, the optical waveguide device **1** may be used as an optical modulator.

Here, the optical waveguide device **1** according to the present embodiment has a surface where the first internal electrode unit **7a** and the signal electrode **5** electrically connected to the ground electrode **6** and the signal electrode **5** face each other. The branching waveguide unit **3c** is interposed between the first internal electrode unit **7a** and the signal electrode **5**.

Compared to the coplanar electrode structure, among the lines of electric force generated by a potential difference given to the signal electrode **5** and the first internal electrode unit **7a**, the lines of electric force going through the branching waveguide unit **3c** in the direction substantially vertical (perpendicular) to the first surface **S1** may be concentrated. In other words, the number of the lines of electric force going through in the direction substantially vertical (perpendicular) to the first surface **S1** may be increased. This may increase the application efficiency of the driving voltage. By increasing

6

the application efficiency of the driving voltage, the power that is required to generate the desired change in the refractive index may be reduced.

Compared to the case of using a conductive crystal material to form an electrode inside the substrate, the power saving may be achieved as described below because the first internal electrode unit **7a** is formed of metal. That is, in the optical waveguide device **1**, a conductor loss by the electrode (**5** or **7a**) may be expressed by the following formula.

$$\alpha_c \propto Rs \propto \frac{1}{\sqrt{\pi f \mu \sigma}}$$

In this case, f indicates a frequency of the voltage that is applied to the signal electrode **5**, σ indicates an electric conductivity of the electrode, and μ indicates a permeability. FIG. 3 illustrates a diagram of a relation of an optical response (modulation efficiency) and a frequency in the optical waveguide device **1**. That is, as illustrated in FIG. 3, the smaller the conductor loss expressed by the above-described formula is, the larger the optical response is. Thus, the modulation efficiency is increased. Since this tendency is remarkable in a high frequency band and is useful in a device such as, for example, an optical modulator, a polarization mode dispersion compensator, or an optical switch used for optical communication.

Therefore, according to the present embodiment, when the first internal electrode unit **7a** is formed of metal, the electric conductivity of the electrode is higher than that of an electrode formed of a conductive crystal material. Thus, the conductor loss may be reduced according to the above-described formula. When the conductor loss is reduced, the modulation efficiency is increased, which may reduce the driving voltage.

As described above, according to the first embodiment, compared to the technique for using a conductive crystal material to form an electrode, the power saving may be achieved by reducing the driving voltage in the first embodiment.

FIG. 4A through FIG. 4D are diagrams illustrating a second embodiment. In FIG. 4A through FIG. 4D, numeral **11** indicates an optical waveguide device. FIG. 4A is a top view of the optical waveguide device **11**. FIG. 4B is an expanded view of a portion of FIG. 4A. FIG. 4C is an A cross sectional view of FIG. 4B. FIG. 4D is a B cross sectional view of FIG. 4B.

The optical waveguide device **11** illustrated in FIG. 4A through FIG. 4D is similar to the optical waveguide device **1** according to the first embodiment (see FIG. 1A through FIG. 1D) in that the optical waveguide device may be used as an optical modulator. However, a ground electrode **16** and an in-substrate electrode **17** of the optical waveguide device **11** shown in FIG. 4A through 4D are different. The same numerals in the FIG. 1A through FIG. 1D indicate substantially similar parts.

Here, a ground electrode **16** includes a second electrode unit **16b** and a first electrode unit **16a** that may be formed when a via part **17b** described below is formed. The first electrode unit **16a** except a part thereof is covered with the second electrode unit **16b**. Numeral **16a'** in FIG. 4A indicates a part where the first electrode unit **16a** is not covered with the second electrode unit **16b**. The pattern of the ground electrode **16** is changeable accordingly.

The in-substrate electrode **17** includes a first internal electrode unit **17a** having a pattern different from that of the in-substrate electrode **7** according to the first embodiment,

and includes the via part 17b. The width of the first internal electrode unit 17a is larger than in the first embodiment. For example, as illustrated in FIG. 4C and FIG. 4D, the width of the first internal electrode 17a is formed to be longer than the distance between the ground electrodes 16 between which the signal electrode 5 is interposed. The via part 17b as an example of the first connection unit is the same as the via part 7b in that a plurality of via parts 17b are formed along the both edges of the width direction of the first internal electrode unit 17a, so that the upper ground electrode 16 and the first internal electrode unit 17a are connective.

However, the distance between the via parts 17b facing each other and between which the branching waveguide unit 3c is interposed corresponds to the width of the above-described first internal electrode unit 17a. Accordingly, the distance is longer than in the first embodiment. Therefore, the distance between the branching waveguide unit 3c and the via part 17b may be longer than in the first embodiment. This makes it possible to increase the degree of concentration of the lines of electric force from the signal electrode 5 on the branching waveguide unit 3c (the electric field component of the crystal z-axis component may be increased) and to increase the electric field application efficiency.

When the first internal electrode unit 17a is formed of metal, the electric conductivity of the electrode is higher than that of the electrode formed of a conductive crystal material. This may reduce the conductor loss. When the conductor loss is reduced, the modulation efficiency is increased. This may reduce the driving voltage.

As described above, the power saving is achieved by reducing the driving voltage in the second embodiment.

FIG. 5A through FIG. 5D are diagrams illustrating a third embodiment. In FIG. 5A through FIG. 5D, numeral 20 indicates an optical waveguide device. FIG. 5A is a top view of the optical waveguide device 20. FIG. 5B is an expanded view of a portion of FIG. 5A. FIG. 5C is an A cross sectional view of FIG. 5B. FIG. 5D is a B cross sectional view of FIG. 5B.

The optical waveguide device 20 illustrated in FIG. 5a-FIG. 5D is similar to the optical waveguide device 11 according to the second embodiment in that the optical waveguide device may be used as an optical modulator. However, the in-substrate electrode 27 thereof is different. The same numerals in FIG. 4A through FIG. 4D indicate substantially similar same parts.

The in-substrate electrode 27 includes a first internal electrode unit (27a-1, 27a-2) having a pattern different from that of the in-substrate electrode 17 according to the second embodiment, and includes a via part 27b. The first internal electrode unit (27a-1, 27a-2) has the same width of the end units 27a-1 of the upstream side and the downstream side in the light propagation direction as that of the in-substrate electrode 17 according to the above-described second embodiment. The width of a middle stream unit 27a-2 between the end units 27a-1 is reduced. As for the first internal electrode unit (27a-1, 27a-2), the width of an end unit 27a-1 of the upstream side and the downstream side in the light propagation direction is the same as that of the in-substrate electrode 17 according to the above-described second embodiment. However, the width of a middle stream unit 27a-2 between the end units 27a-1 is reduced. In other words, the first internal electrode unit (27a-1, 27a-2) includes a pattern such that the width of the end positions from the upstream side to the downstream side in the light propagation direction in the branching waveguide unit 3c is larger than the width of other positions.

A plurality of via parts 27b are formed along the both edges of the above-described end unit 27a-1, so that the first internal

electrode unit (27a-1, 27a-2) and the ground electrode 16 are conductive. The distance between the via parts 27b connected to the end unit 27a-1 ranging from the right to the left in the light propagation direction may correspond to the distance of the area facing the ground electrode 16 in the same manner as in the second embodiment. Accordingly, in the same manner as in the second embodiment, it is possible to increase the degree of concentration of the lines of electric force from the signal electrode 5 on the branching waveguide unit 3c (the electric field component of the crystal z-axis component may be increased) and to increase the electric field application efficiency.

When the first internal electrode unit (27a-1, 27a-2) is formed of metal, the electric conductivity of the electrode is higher than that of the electrode formed of a conductive crystal material. This may reduce the conductor loss. When the conductor loss is reduced, the modulation efficiency is increased. This may reduce the driving voltage.

As described above, in the same manner as in the above-described embodiments, the power saving may be achieved by reducing the driving voltage in the third embodiment.

FIG. 6A through FIG. 6D are diagrams illustrating a fourth embodiment. In FIG. 6A through FIG. 6D, numeral 30 indicates an optical waveguide device. FIG. 6A is a top view of the optical waveguide device 30. FIG. 6B is an expanded view of a portion of FIG. 6A. FIG. 6C is an A cross sectional view of FIG. 6B. FIG. 6D is a B cross sectional view of FIG. 6B.

The optical waveguide device 30 illustrated in FIG. 6A through FIG. 6D is similar to the optical waveguide device according to the above-described embodiments in that the optical waveguide device may be used as an optical modulator. However, an in-substrate electrode 37 thereof is different. The same numerals in FIG. 6A through FIG. 6D indicate substantially similar parts.

The in-substrate electrode 37 includes a first internal electrode unit (37a-1, 37a-2) having a pattern different from that of the in-substrate electrode according to the above-described embodiments. The via part 17b thereof is basically the same as in the second embodiment. Compared to the first internal electrode unit 17a according to the second embodiment, the first internal electrode unit (37a-1, 37a-2) according to the fourth embodiment is formed to have a narrower width of a part to which the via part 17b is not connected. In other words, the first internal electrode unit (37a-1, 37a-2) has a comb-like pattern having a trunk part 37a-1 in a lower position of the branching waveguide unit 3c and also has comb-like branch parts 37a-2 ranging from the right to the left in the light propagation direction. According to the present embodiment, as illustrated in FIG. 6A, the comb-like branch parts 37a-2 formed on the ends of the upstream side and the downstream side in the light propagation direction in the first internal electrode unit (37a-1, 37a-2) are formed to be relatively thicker than other comb-like branch parts 37a-2.

The via part (conduction via) 17b as an example of the first connection unit is connected to one of the comb-like branch parts 37a-2 in the first internal electrode unit (37a-1, 37a-2), so that the first internal electrode unit (37a-1, 37a-2) and the ground electrode 16 are connected. As with the second embodiment, a plurality of via parts 17b may be formed to correspond to the comb-like branch parts 37a-2. In this case, as illustrated in FIG. 6C, each of the via parts 17b may be in a shape to be connected at a top of a branch of one of the comb-like branch parts 37a-2.

Therefore, the via part 17b may connect the first internal electrode unit (37a-1, 37a-2) and the ground electrode 16. The distance between the via parts 17b connected to the comb-like branch parts 37a-2 may correspond to the distance

of the area facing the ground electrode **16** in the same manner as the second embodiment and the third embodiment. Accordingly, as with the second embodiment and the third embodiment, it is possible to increase the degree of concentration of the lines of electric force from the signal electrode **5** on the branching waveguide unit **3c** (the electric field component of the crystal z-axis component may be increased) and to increase the electric field application efficiency.

When the first internal electrode unit (**37a-1**, **37a-2**) is formed of metal, the electric conductivity of the electrode is higher than that of the electrode formed of a conductive crystal material. This may reduce the conductor loss. When the conductor loss is reduced, the modulation efficiency is increased. This may reduce the driving voltage.

As described above, in the same manner as in the above-described embodiments, the power saving may be achieved by reducing the driving voltage in the fourth embodiment.

FIG. **7A** through FIG. **7D** are diagrams illustrating a fifth embodiment. In FIG. **7A** through FIG. **7D**, numeral **40** indicates an optical waveguide device. FIG. **7A** is a top view of the optical waveguide device **40**. FIG. **7B** is an expanded view of a portion of FIG. **7A**. FIG. **7C** is an A cross sectional view of FIG. **7B**. FIG. **7D** is a B cross sectional view of FIG. **7B**.

The optical waveguide device **40** illustrated in FIG. **7A** through FIG. **7D** is similar to the optical waveguide device **11** according to the second embodiment in that the optical waveguide device may be used as an optical modulator. However, the branching waveguide unit **3c** of the optical waveguide **3** thereof is used as a ridge waveguide, for example. That is, as illustrated in FIG. **7C** and FIG. **7D**, for example, a groove **2a** is formed on the both sides of the branching waveguide unit **3c**, so that the branching waveguide unit **3c** is used as a ridge waveguide.

The branching waveguide unit **3c** is used as a ridge waveguide. The use of branching waveguide unit **3c** as a ridge waveguide makes it possible to increase the degree of concentration of the lines of electric force from the signal electrode **5** on the branching waveguide unit **3c** and to increase the electric field application efficiency while promoting light trapping into the optical waveguide **3c**.

In the same manner as in the above-described embodiments, the power saving may be achieved by reducing the driving voltage in the fifth embodiment.

The fifth embodiment has a configuration in which the optical waveguide **3c** of the optical waveguide device **11** according to the second embodiment includes the ridge waveguide. The fifth embodiment may also have a configuration in which the optical waveguide **3** according to other embodiments includes the ridge waveguide.

FIG. **8A** through FIG. **8D** are diagrams illustrating a sixth embodiment. In FIG. **8A** through FIG. **8D**, numeral **50** indicates an optical waveguide device. FIG. **8A** is a top view of the optical waveguide device **50**. FIG. **8B** is an expanded view of a portion of FIG. **8A**. FIG. **8C** is an A cross sectional view of FIG. **8B**. FIG. **8D** is a B cross sectional view of FIG. **8B**.

The optical waveguide device **50** according to the ninth embodiment illustrated in FIG. **8A** through FIG. **8D** is similar to the optical waveguide device according to the above-described embodiments in that the optical waveguide may be used as an optical modulator. However, a ground electrode **56** and an in-substrate electrode **57** thereof are different. The same numerals in FIG. **8A** through FIG. **8D** indicate substantially similar parts.

Here, the ground electrode **56** is formed on the side surface of the substrate **2**. According to the present embodiment, on either one of the longer surfaces along the longitudinal direction of the substrate **2**, the ground electrode **56** is formed from

the upstream side to the downstream side in the light propagation direction in the branching waveguide unit **3c**. The in-substrate electrode **57** includes a second internal electrode unit **57a** having a surface area corresponding to a surface to which the signal electrode **5** applies the electric field in the direction vertical (perpendicular) to the first surface **S1** of the substrate **2** and includes a plurality of branch parts **57b** as an example of a second connection unit that electrically connects the second internal electrode unit **57a** and the ground electrode **56**.

The plurality of branch parts **57b** are formed at intervals in the light propagation direction in the branching waveguide unit **3c** and extend from the second internal electrode unit **57a** to the side of the substrate **2** where the ground electrode **56** is formed. As illustrated in FIG. **8C**, the A cross sectional view in FIG. **8B** corresponds to the cross sectional view in which the branch part **57b** is not formed. The B cross sectional view in FIG. **8B** corresponds to the cross sectional view in which the branch part **57b** is formed as illustrated in FIG. **8D**.

In the optical waveguide device **50** configured as described above, the in-substrate electrode **57** forms a cavity in a part where the in-substrate electrode **57** is to be formed (see FIG. **2A** through FIG. **2C**) in the same manner as in the above-described first embodiment, the formed cavity is filled with metal as the in-substrate electrode **57** (see FIG. **2D** and FIG. **2E**), and then the electrode **5** is formed on the first surface **S1** of the substrate **2**, and the electrode **56** is formed on the side surface of the substrate **2**.

As illustrated in FIG. **8C** and FIG. **8D**, when the in-substrate electrode **57** is filled with the metal, a part **56a** may be formed as part of the metal, filled in the substrate **2**, and exposed on the side surface. The part **56a** may be configured as an element of the ground electrode **56**. That is, after filling with the metal as described above, the ground electrode **56** may be formed by forming an electrode layer **56b** having a pattern covering the part **56a**.

In the optical waveguide device **50**, the branching waveguide unit **3c** is interposed between the second internal electrode unit **57a** and the signal electrode **5** that are electrically connected to the ground electrode **56**.

Compared to the coplanar electrode structure, among the lines of electric force generated by the potential difference given to the signal electrode **5** and the first internal electrode unit **57a**, the lines of electric force going through the branching waveguide unit **3c** in the direction vertical (perpendicular) to the first surface **S1** may be concentrated. In other words, the number of lines of electric force going through in the vertical (perpendicular) direction may be increased. This may improve the application efficiency of the driving voltage. The improvement of the application efficiency of the driving voltage may reduce the power required to generate a desired change in the refractive index.

When the first internal electrode unit **57a** is formed of the metal, the electric conductivity of the electrode is higher than that of the electrode formed of a conductive crystal material. This may reduce the conductor loss. If the conductor loss is reduced, the modulation efficiency is increased. This may reduce the driving voltage.

In the same manners as in the above-described embodiments, the power saving may be achieved by reducing the driving voltage in the sixth embodiment.

FIG. **9A** through FIG. **9D** are diagrams illustrating a seventh embodiment. In FIG. **9A** through FIG. **9D**, numeral **60** indicates an optical waveguide device. FIG. **9A** is a top view of the optical waveguide device **60**. FIG. **9B** is an expanded

11

view of a portion of FIG. 9A. FIG. 9C is an A cross sectional view of FIG. 9B. FIG. 9D is a B cross sectional view of FIG. 9B.

The optical waveguide device 60 illustrated in FIG. 9A through FIG. 9D is similar to the optical waveguide device 50 according to the above-described sixth embodiment in that the optical waveguide device may be used as an optical modulator. However, the in-substrate electrode 67 of the optical waveguide device 60 is different from the in-substrate electrode 57 of the sixth embodiment. The same numerals in FIG. 9A through FIG. 9D indicate substantially similar parts.

Here, the in-substrate electrode 67 includes a second internal electrode unit 67a having a surface area corresponding to a surface to which the signal electrode 5 applies the electric field in the vertical (perpendicular) direction to the first surface S1 of the substrate 2, and also includes an electrode unit 67b as an example of the second connection unit used to electrically connect the second internal electrode unit 67a and the ground electrode 56.

The extended electrode unit 67b, an extended area formed as a part of the in-substrate electrode 67 when the second internal electrode unit 67a is formed, is formed to extend to the side part where the ground electrode 56 is formed from the second internal electrode unit 67a in a part from the upstream side to the downstream side in the light propagation direction in the branching waveguide unit 3c.

A seventh embodiment also includes the in-substrate electrode 67 formed of the metal provided inside the substrate 2. Therefore, as with the cases of the above-described embodiments, the power saving may be achieved by reducing the driving voltage.

FIG. 10 is a cross sectional view of an optical waveguide device 70 according to an eighth embodiment. The optical waveguide device 70 includes a substrate 72, an optical waveguide 73, electrodes 75 and 76, and in-substrate electrodes 77a and 77b. The substrate 72 is formed of LN, which is an example of the electro-optic crystal. Unlike the above-described embodiments, the electric field change in the direction horizontal (parallel) to the first surface S1 causes a change in the refractive index of the optical waveguide 73. Specifically, an X-cut LN substrate 72 may be used.

The optical waveguide 73 is provided on the first surface S1 of the substrate 72. For example, the pattern of the Mach-Zehnder interferometer may be used in the same manner as in the above-described embodiments. In this case, the optical waveguide device 70 may be used in the same manner as in the above-described embodiments. The pattern of the optical waveguide 73 is an example. Any other pattern may be used.

The electrodes 75 and 76 are formed on the top of the first surface S1 of the substrate 72 to operate with respect to the optical waveguide 73. For example, the electrode 75 may be a signal electrode, and the electrode 76 may be a ground electrode (GND). In this case, the electrodes 75 and 76 are formed across the upper part of the optical waveguide 73.

The electrode 75 includes a second electrode unit 75b as a metal layer and a first electrode unit 75a connected to the second electrode unit 75b. The first electrode unit 75a is used to connect an in-substrate electrode 77a and the second electrode unit 75b composing the electrode 75. As with the above-described first electrode unit 6a illustrated in FIG. 2, the first electrode unit 75a may be formed to be combined with the in-substrate electrode 77a described below.

In the same manner, the electrode 76 includes a second electrode unit 76b as a metal layer and a first electrode unit 76a connected to the second electrode unit 76b. The first electrode unit 76a is formed to be connected to the in-substrate electrode 77b and the second electrode unit 76b com-

12

posing the electrode 76. As with the first electrode unit 6a illustrated in FIG. 2, the first electrode unit 76a may be formed to be combined with the in-substrate electrode 77b.

Numerals 74 indicates a buffer layer that is layered between the substrate 72 and the electrodes 75 and 76.

The in-substrate electrodes 77a and 77b are formed of metal, for example, copper. According to the example illustrated in FIG. 2, a cavity is formed inside the substrate 72 that is to be the in-substrate electrodes 77a and 77b, and the formed cavity is filled with metal material (for example, copper or the like).

By forming the part of the metal exposed on the side surface of the substrate 72 at the same time when the in-substrate electrodes 77a and 77b are formed by filling the metal, e, the part may be formed as the first electrode units 76a and 76b.

Accordingly, the in-substrate electrodes 77a and 77b may be connected to the electrodes 75 and 76, respectively. When the electrode 75 is a signal electrode and the electrode 76 is a ground electrode, the voltage from the signal electrode 75 and the ground electrode 76 may be applied to the in-substrate electrodes 77a and 77b, respectively.

When the optical waveguide 73 is a pattern of the Mach-Zehnder interferometer illustrated in the above-described embodiments, the in-substrate electrodes 77a and 77b may be formed at intervals and either of the two branching waveguide units (Numerals 3c and 3d) may be interposed between the in-substrate electrodes 77a and 77b. In this case, the in-substrate electrode 77a may be operated as a traveling wave electrode used to apply the electric field to the branching waveguide unit 3c by cooperating with the electrode 75. A high frequency electric signal according to transmission data is supplied from one end of the in-substrate electrode 77a and the other end may be terminated.

The in-substrate electrodes 77a and 77b have a surface arranged in a direction vertical (perpendicular) to the first surface S1 of the substrate 72, are formed to face each other, and the optical waveguide 73 is interposed between the in-substrate electrodes 77a and 77b. In other words, the in-substrate electrodes 77a and 77b are an example of a pair of third internal electrode units. Accordingly, the optical waveguide 73 interposed by the in-substrate electrodes 77a and 77b may generate a line of electric force in the direction horizontal (parallel) to the substrate 72 according to the voltage applied between the in-substrate electrodes 77a and 77b.

For example, compared to the electrode structure that has the signal electrodes 75 and 76 without having the in-substrate electrodes 77a and 77b, the signal electrode 75 and the ground electrode 76 are formed on the top of the substrate 72, so that the line of electric force is generated between the surfaces parallel to the first surface S1 by the voltage application. Therefore, compared to the case of forming the in-substrate electrodes 77a and 77b having the surface in the direction vertical (perpendicular) to the first surface S1 of the substrate 72 and facing each other, the generated intensity of electric field that is horizontal (parallel) to the first surface S1 of the substrate 72 may be expected to be limited at the same driving voltage.

That is, among the lines of electric force generated by the potential difference given to the electrodes 75 and 76, the lines of electric force going through the optical waveguide 73 in the direction parallel to the first surface S1 may be concentrated by the in-substrates electrodes 77a and 77b. In other words, the number of the lines of electric force going through in the direction horizontal (parallel) to the first surface S1 may be increased. This may increase the application efficiency of the driving voltage. By increasing the application effi-

13

ciency of the driving voltage, the power required to generate a desired change in the refractive index may be reduced.

The first electrode units **75a** and **76a** according to the present embodiment include parts that are extended and formed above the optical waveguide **73** from the formation areas of the second electrode units **75b** and **76b**, respectively. Therefore, even if a longer distance is provided between the signal electrode **75** and the ground electrode **76**, the distance between the in-substrate **77a** and **77b**, between with the optical waveguide **73** is interposed, may be narrowed. The extended areas of the first electrode unit **75a** and **76a** work as bridges to the in-substrate electrodes **77a** and **77b** corresponding to the electrodes **75** and **76**.

If the in-substrate electrodes **77a** and **77b** are formed of metal, the electric conductivity of the electrode is higher than that of the electrode formed of a conductive crystal material. This may reduce the conductor loss. When the conductor loss is reduced, the modulation efficiency is increased. This may reduce the driving voltage.

In the same manner as in the above-described embodiments, the power saving may be achieved by reducing the driving power in the eighth embodiment.

FIG. **11** is a cross sectional view of an optical waveguide device **80** according to the ninth embodiment. The optical waveguide device **80** according to the ninth embodiment is basically the same as the optical waveguide device **70** of the eighth embodiment except that the optical waveguide **83** thereof is formed inside the substrate **72**. In FIG. **11**, the same numerals as in FIG. **10** indicate the substantially similar parts.

The size of a surface vertical (perpendicular) to the first surface **S1** in the in-substrate electrodes **77a** and **77b** of the optical waveguide device **80** may be specified to be large enough to make the line of electric force, horizontal (parallel) to the first surface **S1**, go through the optical waveguide **83** formed inside the substrate **72**. Therefore, as for the in-substrate electrodes **77a** and **77b** illustrated in FIG. **11**, cavities are formed from the first surface **S1** to be deeper than in the case of FIG. **10**, and the formed cavities may be filled with metal.

In the same manner as the above-described eighth embodiment, the power saving is achieved by reducing the driving voltage in the ninth embodiment.

FIG. **12** is a cross sectional view of an optical waveguide device **90** according to the tenth embodiment. The optical waveguide device **90** according to the tenth embodiment corresponds to a modification of the optical waveguide device **80** according to the ninth embodiment.

That is, the optical waveguide device **90** includes electrodes **95** and **96** that are different from those in the optical waveguide device **80** illustrated in FIG. **11** and also includes the in-substrate electrodes **97a** and **97b**.

Here, the electrodes **95** and **96** may be used as, for example, a signal electrode and a ground electrode, respectively. The electrodes **95** and **96** includes first electrode units **95a** and **96a** that may be formed when the in-substrate electrodes **97a** and **97b** are formed, and also includes second electrode units **95b** and **96b** that are connected to the first electrode units **95a** and **96a**. The first electrode units **95a** and **96a** are covered with the second electrode units **95b** and **96b**, respectively. The pattern of the electrodes **95** and **96** is changeable accordingly.

The in-substrate electrodes **97a** and **97b** have a pattern different from that of the in-substrate electrodes **77a** and **77b** according to an eleventh embodiment. Specifically, the in-substrate electrodes **97a** and **97b** include the third internal electrode units **97a-1** and **97b-1** and the connection units **97a-2** and **97b-2**, respectively. The third internal electrode units **97a-1** and **97b-1** are formed in a pair facing each other

14

and have surfaces in the direction vertical (perpendicular) to the first surface **S1** of the substrate **72**. The optical waveguide **83** is interposed between the third internal electrode units **97a-1** and **97b-1**.

The connection unit **97a-2** and the third internal electrode unit **97a-1** are formed of metal to be combined with the first electrode unit **95a** composing the electrode **95**. Accordingly, the third internal electrode unit **97a-1** is connected to the electrode **95** via the first electrode unit **95a** of the electrode **95**. In the same manner, the connection unit **97b-2** and the third internal electrode unit **97b-1** are formed of metal to be combined with the first electrode unit **96a** composing the electrode **96**. Accordingly, the third internal electrode unit **97b-1** is connected to the electrode **96** via the first electrode unit **96a**.

The first electrode units **95a** and **96a** illustrated in FIG. **11** are covered with the second electrode units **95b** and **96b**. Unlike the numerals **75a** and **76a** in FIG. **10**, the extended areas are not included. In FIG. **12**, however, the first electrode units **95a** and **96a** are connected to the connection units **97a-2** and **97b-2**. Even when the distance between the electrodes **95** and **96** is relatively longer, the distance between the third internal electrode units **97a-1** and **97b-1** may be narrowed as a pair.

That is, among the lines of electric force generated by the potential difference given between the electrodes **95** and **96**, the lines of electric force going through in the direction horizontal (parallel) to the first surface **S1** may be concentrated. In other words, the number of the lines of electric force going through in the direction horizontal (parallel) to the first surface **S1** may be increased. This may increase the application efficiency of the driving voltage. By increasing the application efficiency of the driving voltage, the power required to generate a desired change in the refractive index may be reduced.

In the same manner as in the above-described seventh embodiment and the eighth embodiment, the power saving is achieved by reducing the driving voltage in the tenth embodiment.

The connection units **97a-2** and **97b-2** are formed in an L-shape as illustrated in FIG. **12**. The connection units **97a-2** and **97b-2** may be formed in any shape. The shape of the connection unit **97b-2** along the longitudinal direction of the optical waveguide **83** may be formed accordingly. For example, the shape may be formed in a continuous shape or a comb-like shape.

Regardless of the above-described embodiments, the various changes, substitutions, and alterations could be made hereto without departing from the spirit and scope of the invention.

For example, in the first to seventh embodiments, the optical waveguide **3** may be formed inside the substrate **2**. The via parts **7b**, **17b**, and **27b** are formed in the direction vertical (perpendicular) to the first surface **S1** or may be formed in the direction oblique to the first surface **S1**.

In the above-described embodiments, an optical waveguide may be provided on both the first surface **S1** of the substrate **2** and inside the substrate **2**. For example, when a three-dimensional intersecting waveguide or the like is formed, the optical waveguides are provided both on the first surface **S1** and inside the substrate **2**. In this case, the in-substrate electrode may be formed accordingly to apply the voltage to the waveguide inside the substrate and/or the waveguide on the substrate surface.

In the eighth to tenth embodiments, according to the sixth and seventh embodiments, the electrodes **75** and **95** as signal electrodes and the electrodes **76** and **96** as ground electrodes may be formed on different substrates.

15

As described above, the substrate **2** includes the optical waveguide devices **1**, **11**, **20**, **30**, **40**, **50**, **60**, **70**, **80**, and **90** that are used as an optical modulator. The optical waveguide devices may be used as various optical modulators.

For example, a polarization mode dispersion compensator or a polarization scrambler described in the document for reference (“8 Channel LiNbO₃ Polarization Controllers and Variable Differential Group Delay for PMD Compensation,” Doi Masaharu et al, the IEICE General Conference 2008) and the disclosed optical waveguide device may be used. Furthermore, an optical switch described in the document for reference (“Low-crosstalk operation of LiNbO₃ optical switch having sub Mach-Zehnder structures,” Chiba Akito et al, the Society Conference of IEICE 2006) and the disclosed optical waveguide device may be used.

All examples and conditional language recited herein are intended for pedagogical purposes to aid the reader in understanding the invention and the concepts contributed by the inventor to furthering the art, and are to be construed as being without limitation to such specifically recited examples and conditions, nor does the organization of such examples in the specification relate to a showing of the superiority and inferiority of the invention. Although the embodiment(s) of the present inventions have been described in detail, it should be understood that the various changes, substitutions, and alterations could be made hereto without departing from the spirit and scope of the invention.

16

What is claimed is:

1. A method comprising:

forming an optical waveguide on a substrate and/or inside the substrate, the substrate having an electro-optical effect;

forming an in-substrate electrode of metal inside the substrate;

arranging a signal electrode over the optical waveguide; and

arranging a ground electrode over a first surface of the substrate and separated by a distance from the signal electrode;

forming a via hole; and

creating a connection between the ground electrode and the in-substrate electrode through a via-hole provided in the substrate.

2. The method according to claim **1**, the method further comprising:

condensing and radiating an ultrashort pulse laser onto a part of the substrate where the in-substrate electrode is to be formed, and selective etching after the part is amorphized or performing ablation on the part.

3. The method according to claim **1**, wherein forming the in-substrate electrode includes

forming a cavity within the substrate; and

filling the cavity with the metal to form the in-substrate electrode.

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